

IPD series for Automotive

8ch Low-side switch

BD8LB600FS-C

Features

- Monolithic power IC that has a built-in control part (CMOS) and a power MOS FET on 1chip
- 8ch Low-side switch for driving resistive, inductive, capacitive load
- 16bit Serial peripheral interface(SPI) for diagnostics and control
- Built-in Open Load Detection circuit in output-off state
- Built-in Self restart Over Current Protection circuit (OCP)
- Built-in Over Voltage Protection for Output circuit
- Built-in Self restart Over Heating Protection circuit (TSD)
- Low On resistance of R_{ON}=600mΩ(V_{IN}=5V, Tj=25°C, I_{Dn}=0.2A)
- Surface mount SSOP-A24 Package
- AEC-Q100 Qualified⁽¹⁾
 (1)Grade 1

Overview

BD8LB600FS-C is an Automotive 8ch Low-Side switch. It has a built-in Over Current Protection circuit, Thermal Shutdown circuit, Open Load Detection circuit, Under Voltage Lock Out circuit, and has a Diagnostic Output(SO) function during abnormal detection.

Application

8ch Low-side switch for driving resistive, inductive, capacitive load

Product Summary

Digital part Operating voltage	3.0V to 5.5V
Analog part Operating voltage	4.0V to 5.5V
On-state resistance(25°C,Typ)	600mΩ
Over current limit(Typ)	1.80A
Active clamp energy(25°C)	70mJ

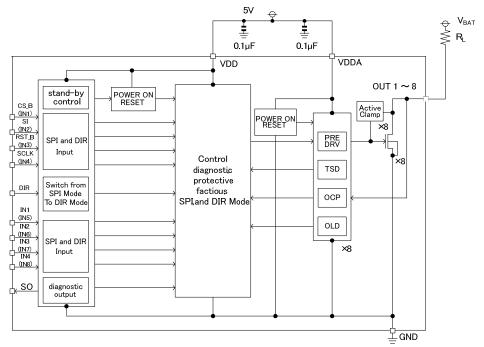
Package

SSOP-A24

10.00mm x 7.80mm x 2.10mm



Basic Application Circuit (Recommendation)



OProduct configuration: Silicon monolithic integrated circuit OThe product is not designed for radiation resistance.

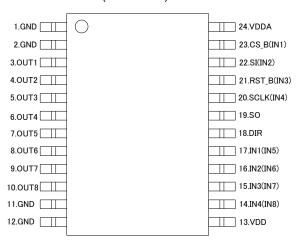
Pin Descriptions

Pin	Symbol		I/O ⁽¹⁾	Function
1	GND		-	GND
2	GND		-	GND
3	OUT1		0	Channel 1 output
4	OUT2		0	Channel 2 output
5	OUT3		0	Channel 3 output
6	OUT4		0	Channel 4 output
7	OUT5		0	Channel 5 output
8	OUT6		0	Channel 6 output
9	OUT7		0	Channel 7 output
10	OUT8		0	Channel 8 output
11	GND	-		GND
12	GND		-	GND
13	VDD		-	Digital power supply
14	IN4(IN8)	-	PD	Control input for Channel 4 and 8 (DIR=L) / Control input for Channel 8 (DIR=H)
15	IN3(IN7)	I	PD	Control input for Channel 3 and 7 (DIR=L) / Control input for Channel 7 (DIR=H)
16	IN2(IN6)	I	PD	Control input for Channel 2 and 6 (DIR=L) / Control input for Channel 6 (DIR=H)
17	IN1(IN5)	I	PD	Control input for Channel 1 and 5 (DIR=L) / Control input for Channel 5 (DIR=H)
18	DIR	_	PD	SPI mode, DIR mode change input terminal
19	SO	0		Serial data output terminal
20	SCLK(IN4)	I PD		Serial clock (DIR=L) / Control input for Channel 4 (DIR=H)
21	RST_B(IN3)	I PD		Reset terminal (DIR=L) / Control input for Channel 3 (DIR=H)
22	SI(IN2)	ı	PD	Serial data input (DIR=L) / Control input for Channel 2 (DIR=H)
23	CS_B(IN1)	I	PU/PD ⁽²⁾	SPI enable input (DIR=L) / Control input for Channel 1 (DIR=H)
24	VDDA	-		Analog power supply

O : Output terminal, I : Input terminal

Pin Configurations

SSOP-A24 (TOP VIEW)



PD: Pull Down terminal, PU: Pull Up terminal
Pull Up at DIR=Low setting, Pull Down at DIR=High

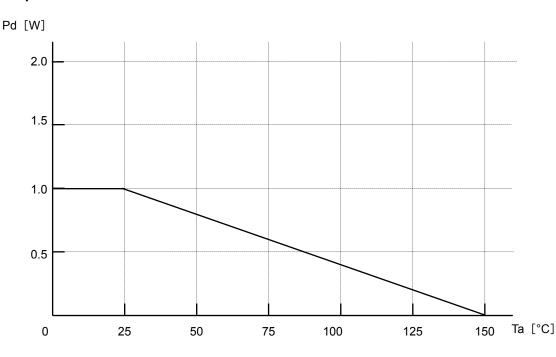
Absolute Minimum Ratings

Item		Symbol	Limit values	Unit
DRAIN-SOURCE voltage		V _{DS}	45(Internally limited)	V
Power supply voltage (Logic)		V_{DD}	7 (1)	V
Power supply voltage (Analog	g)	V _{DDA}	7	V
Diagnostic output voltage		Vso	-0.3 to +7	V
Output current (DC)		Гоит	1.0(Internally limited) (2)	А
Output current (Pulse)		I _{OP}	Internally limited (3)	А
Input voltage		Vin	-0.3 to +7	V
Power consumption		Pd	1.0(SSOP-A24) (4)	W
Operating temperature range		Topr	-40 to +150	°C
Storage temperature range		T _{stg}	-55 to +150	°C
Maximum junction temperature		T _{jmax}	150	°C
Active clamp energy	$(T_{j(0)} = 25^{\circ}C)$	-	70 (5)	mJ
(single pulse)	$(T_{j(0)} = 150^{\circ}C)$	E _{AV}	50 ⁽⁶⁾	mJ

Operating Voltage Ratings

Item	Code	Limit values	Unit
Digital part Operating voltage	V_{DD}	3.0 to 5.5	V
Analog part Operating voltage	V _{DDA}	4.0 to 5.5	V

Heat Dissipation Characteristic



(SSOP-A24) IC mounted on ROHM standard board (70×70*1.6[mm], glass epoxy 1 layer board). Derate by 8.0mW/°C above 25°C.

⁽¹⁾ However, V_{DD} < V_{DDA} + 0.3V
(2) However, exceed neither Pd nor ASO.
(3) Internally limited by the overcurrent limiting circuit.

⁽⁴⁾ IC mounted on ROHM standard board (70×70*1.6[mm], glass epoxy 1 layer board). Derate by 8.0mW/°C above 25°C.

 ⁽⁵⁾ Min Active clamp energy at T_{I(0)} = 25°C, using single non-repetitive pulse of 0.5A
 (6) Min Active clamp energy at T_{I(0)} =150°C, using single non-repetitive pulse of 0.5A. Not 100% tested.

Electrical Characteristics (unless otherwise specified, VDDA=5V,VDD=5V,-40°C \leq Tj \leq +150°C)

Item	Symbol		Limit values	S	Unit	Condition
[Power Supply Block]	Cymbol	Min	Тур	Max	Orne	Condition
VDDA Standby current (All output on standby mode)	I _{DDAS}	-	0	20	μA	VDDA=VDD=5V, CS_B=5V, RST_B=0V
VDD Standby current (All output on standby mode)	I _{DDS}	-	0	20	μΑ	VDDA=VDD=5V, CS_B=5V, RST_B=0V
VDDA Operating current)	I _{DDA}	-	2	5	mA	VDDA=VDD=5V
VDD Operating current)	I _{DD}	-	0.5	1	mA	VDDA=VDD=5V
VDDA power on reset Threshold Voltage	VPORA	-	-	4.0	٧	
VDD power on reset Threshold Voltage	V _{POR}	-	-	2.7	V	
[Input PIN]				\/DD::0.0		
L level input voltage	VINL	0	-	VDD×0.2	V	
H level input voltage	V _{INH}	VDD×0.7	-	VDD	V	
Input Hysteresis	V _H YS	0.1	0.3	0.5	V	
L level input current 1 (RST_B,DIR,IN1 to IN4,SCLK,SI)	I _{INL1}	-10	0	10	μA	RST_B=DIR=IN1 to IN4=SCLK =SI=0V
L level input current 2(CS_B)	I _{INL2}	-100	-50	-25	μΑ	CS_B(DIR=L)=0V
H level input current 1 (RST_B,DIR,IN1 to IN4,SCLK,SI)	l _{INH1}	25	50	100	μΑ	RST_B=DIR=IN1 to IN4=SCLK =SI=5V
H level input current 2(CS_B)	I _{INH2}	-10	0	10	μΑ	CS_B(DIR=L)=5V
[Power MOS Output]	ii.					
Output ON resistance	Proyous	-	0.6	0.8	Ω	VDD=VDDA=5V, I _{DS} =0.2A, Tj=25°C
Output ON resistance	R _{DS(ON)}	-	1.1	1.4	Ω	VDD=VDDA=5V, I _{DS} =0.2A, Tj=150°C
Output sink current	luces.	-	10	20	μA	V _{DS} =30V, Tj=25°C
Output sink current	I _{L(OFF)}	-	15	40	μA	V _{DS} =30V, Tj=150°C
Output leak current (Open load detected)	loL	25	50	100	μΑ	V _{DS} =40V
Switching time	ton	-	20	50	μs	$ \begin{array}{c} VDD=VDDA=5V,CS_B=0V/5V, \\ R_L=60\Omega,VB=12V \end{array} $
Switching time	toff	-	20	50	μs	VDD=VDDA=5V,CS_B=0V/5V, $R_L=60\Omega$,VB=12V
Slew rate on	dV/dton	0.3	1	3	V/µs	VDD=VDDA=5V,CS_B=0V/5V, R _L =60Ω,VB=12V
Slew rate off	-dV/dt _{OFF}	0.3	1	3	V/µs	VDD=VDDA=5V,CS_B=0V/5V, R_L =60 Ω ,VB=12V
PWM Output range	f _{PWM}	-	-	1.2	kHz	VDD=VDDA=5V,INn=0V/5V, R _L =60Ω,VB=12V
Output clamp voltage	VcL	45	50	55	V	I _{DS} =1mA(at Output turn off)
Minimum Output Voltage (Load short-circuited)	V _{DS(S)}	31	-	-	٧	INn ⁽¹⁾ =5V,RL=0Ω

⁽¹⁾ n means ch number

Electrical Characteristics (unless otherwise specified, VDDA=5V,VDD=5V,-40°C ≤Tj ≤+150°C)

Item	Symbol		Limit values	3	Unit	Condition	
Item	Symbol	Min	Тур	Max	Offic	Condition	
[Serial Output]							
L level output voltage	V_{SOL}	-	0.3	0.6	V	I _{SO} =1mA	
H level output voltage	V_{SOH}	VDD-0.6	VDD-0.3	1	V	I _{SO} =-1mA	
Serial out output leak current	I _{SO(OFF)}	-5	0	5	μA		
[Protect circuit]							
Over current detection current	$I_{\text{OCP(ON)}}$	1.00	1.80	3.00	Α		
Over current release current	I _{OCP(OFF)}	0.70(1)	1.26(1)	2.10(1)	Α		
Over current detection time	tocp	50	250	600	μs		
Open Load release voltage	$V_{\text{OLD(ON)}}$	0.70	1.50	2.70	V	INn ⁽²⁾ =0V	
Open load detection threshold voltage	V _{OLD(OFF)}	1.00	1.75	3.00	V	INn ⁽²⁾ =0V	
Open load detection time	told	50	300	600	μs	INn ⁽²⁾ =0V	

⁽¹⁾ Not 100% tested

Definition

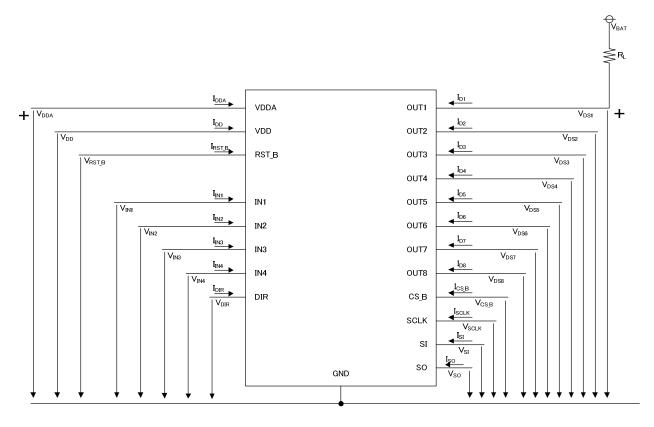


Figure 1. Definition

⁽²⁾ n means ch number

Measurement Circuit

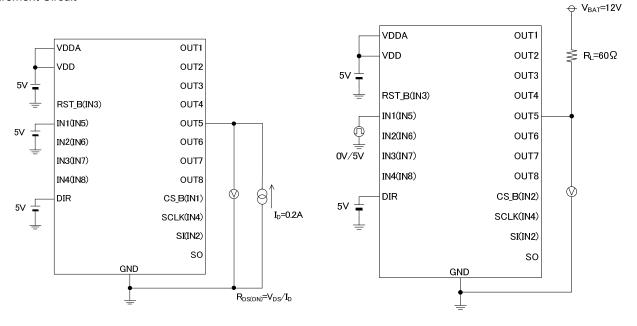
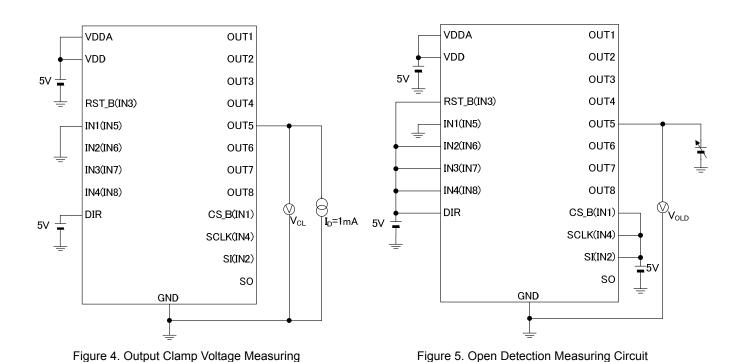


Figure 2. Output ON Resistance Measuring Circuit Diagram

Figure 3. Switching Time Measuring Circuit Diagram



Circuit Diagram

Diagram

DIR(Direct)mode Diagnostic Output Truth Table

VIN	T;	OUTPUT		mode	Vso	Output state	
VIN	Tj	V_{DS}	ID	mode	Vso	Output state	
	Tj < 175°C(Typ) -		I _D ≤ 1.8A(Typ)		L	ON	
Н	1] < 175 C(1yp)	-	I _D > 1.8A(Typ)	Over current detection	Н	OFF	
	Tj ≥ 175°C(Typ)	-	-	Thermal shut down	Н	OFF	
	H (3.0Vor mo		-	Normal	L	OFF	
L	-	L (1.5V(Typ) or less)	-	Open load detection	Н	OFF	

Characteristic Data (Reference Data) (VDD=5V, VDDA=5V, IN=5V, Tj=25°C unless otherwise is specified)

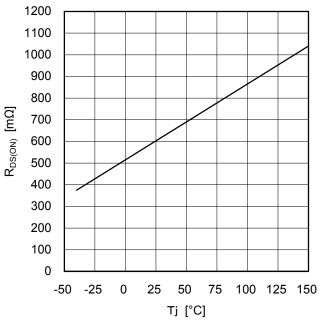


Figure 6. Output ON Resistance Characteristic [Temperature Characteristic]

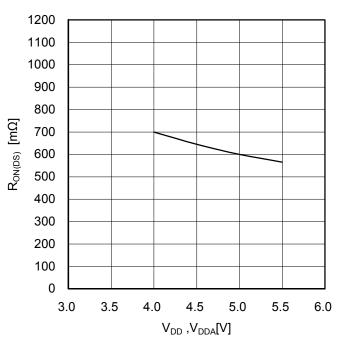


Figure 7. Output ON Resistance Characteristic [Source Voltage Characteristic]

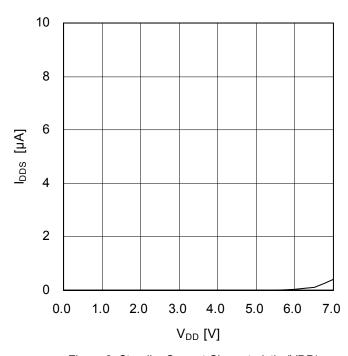


Figure 8. Standby Current Characteristic (VDD)

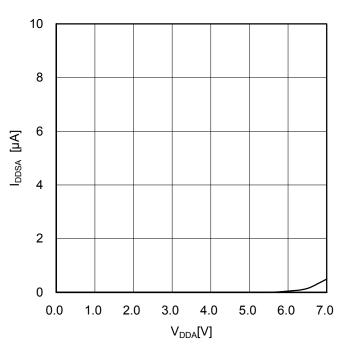


Figure 9. Standby Current Characteristic (VDDA)

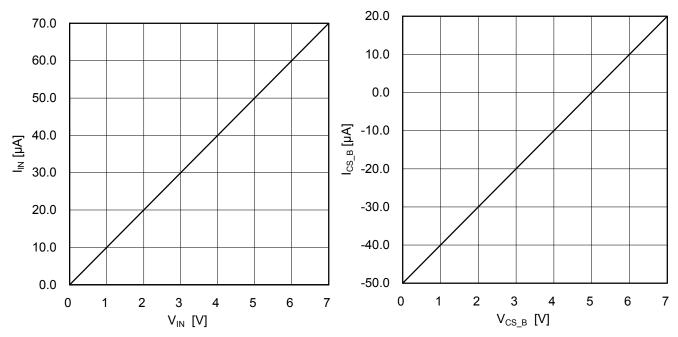


Figure 10. Input current Characteristic (IN1 to 4, DIR, SCLK, SI, RST_B)

Figure 11. Input current Characteristic (CS_B)

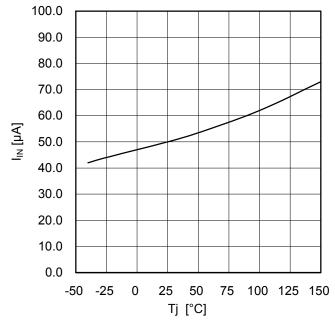


Figure 12. Input current Characteristic

[Temperature Characteristic]

(IN1 to 4, DIR, SCLK, SI, RST_B=5V, CS_B=0V)

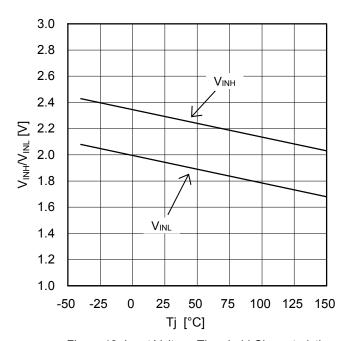
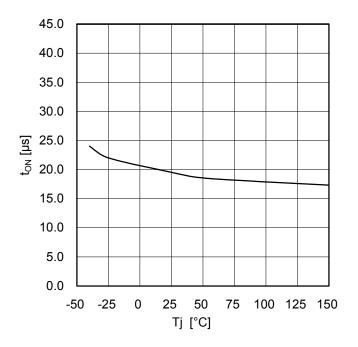


Figure 13. Input Voltage Threshold Characteristic [Temperature Characteristic]



45.0 40.0 35.0 30.0 25.0 20.0 15.0 10.0 5.0 0.0 -50 -25 0 25 50 75 100 125 150 Tj [°C]

Figure 14. Switching Time (ton) [Temperature Characteristic]

Figure 15. Switching Time (t_{OFF}) [Temperature Characteristic]

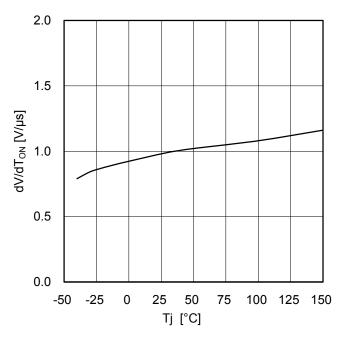


Figure 16. Slew Rate (at ON) [Temperature Characteristic]

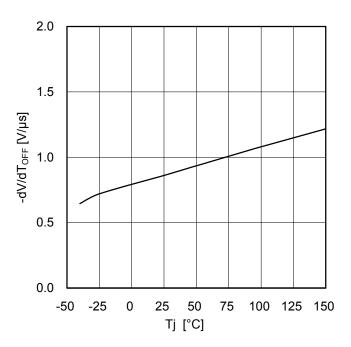


Figure 17. Slew Rate (at OFF) [Temperature Characteristic]

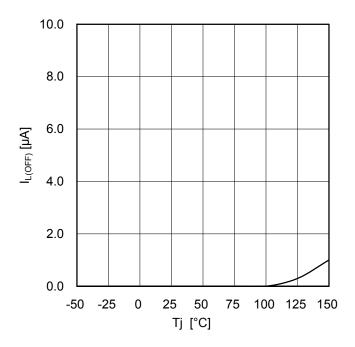


Figure 18. Output Leak Current [Temperature Characteristic](VDS=30V)

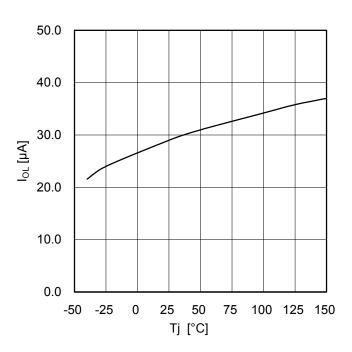


Figure 19. Output Leak Current (Open detect) [Temperature Characteristic] (VDS=40V)

Switching Time Measurement

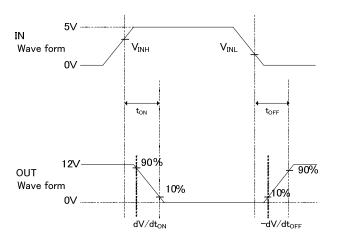


Figure 20. Switching Time

Timing Chart with Inductive Load

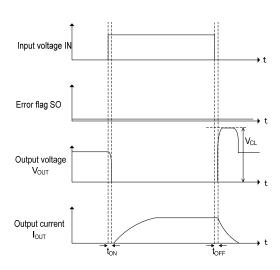


Figure 21. Timing Chart with inductive Load

Pin Symbol I/O Equivalent Circuits 1.2 1.1 1.2 GND	O Equivalent C	ircuits	
11,12 3 to 10 OUT1 to OUT8 13 VDD INA(IN8)		Symbol	I/O Equivalent Circuits
3 to 10 OUT1 to OUT8 13 VDD IN4(IN8), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN8), IN3(1,2, 11,12	GND	
19 SO IN4(IN8), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN7), IN3(IN8), IN1(IN8),		OUT1 to OUT8	x 9
14 to 17 18 20 to 22 NA(INS), INA(INS), IN	13	VDD	
19 SO SO SO SO SO SO SO SO	18	IN3(IN7), IN2(IN6), IN1(IN5), DIR, SCLK(IN4),	IN4(IN8), IN3(IN7), IN2(IN6), IN1(IN5), DIR, SCLK(IN4), RST_B(IN3), SI(IN2)
23 CS_B CS_B CS_B GND	19	SO	50Ω \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
24 VDDA	23	CS_B	LOGIC Ο 100kΩ 50Ω 1kΩ 100kΩ
	24	VDDA	

SPI mode(DIR=L)

When CS B=H,

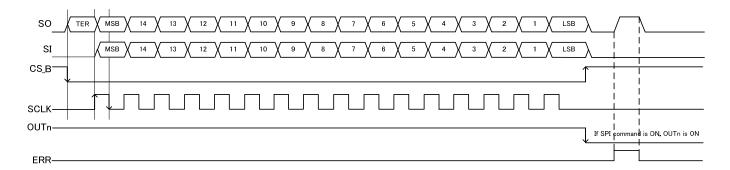
OR signal (ERR) of SI and abnormal signal (TER, TSD, OCP, OLD) is output to SO terminal.

When CS_B=L,

Internal state (TSD, OCP, OLD) is latched at falling edge of CS_B, and output to SO at rising edge of SCLK.

SI is taken in register at falling edge of SCLK.

Output corresponding to each resister input is controlled at rising edge of CS_B.



Definitions of SI and SO signals are shown below.

SI signals

					I	nitial:0x	(0000								
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
IN	18	11	N7	IN	16 	ΙΝ	 	II.	 14	I۱	13	11	 √2	IN	J1
l			I		I		I		I		I		İ		

Bits	INn	States of output and protective circuits						
Dits	IINII	Output	OCP	TSD	OLD			
15:14, 13:12,	00	OFF	disable	disable	disable			
13.12, 11:10, 9:8,	01	ON/OFF (1)	enable/disable	enable/disable	disable/enable			
7:6, 5:4,	10	ON	enable	enable	disable			
3:2, 1:0	11	OFF	disable	disable	enable			

(1) When INn=01, output is controlled by IN terminal.

Output controlled by each input is shown below.

Input	Controlled output
IN1(IN5)	OUT1
IN2(IN6)	OUT2
IN3(IN7)	OUT3
IN4(IN8)	OUT4
IN1(IN5)	OUT5
IN2(IN6)	OUT6
IN3(IN7)	OUT7
IN4(IN8)	OUT8

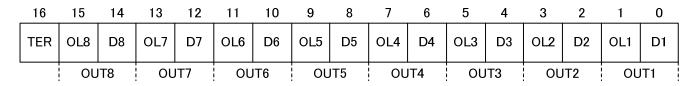
SO signals

When CS B=H,

OR signal (ERR) of abnormal signal (SI, TER, TSD, OCP, OLD) is output to SO terminal.

When CS B=L,

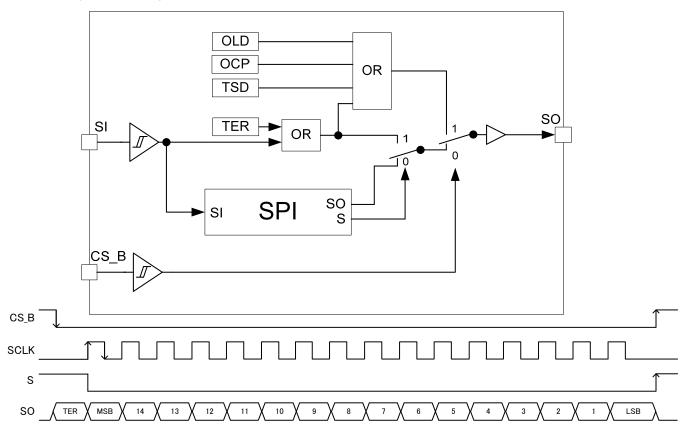
Explanation of each Bit is shown below.



Bits	Data	STATE
16 ⁽¹⁾	0	Correspondence just after reset and normal operation
10 (")	1	Correspondence error of last time
15,13,11	0	Normal operation
9,7,5 3,1	1	Load open
14,12	0	Normal operation
10,8,6 4,2,0	1	OCP or TSD

(1) TER bit outputs logical sums of TER signal and input signal of this device with SI signal in the interval from fall of CS_B to rise of SCLK as shown below.

Block diagram and timing chart are shown below.

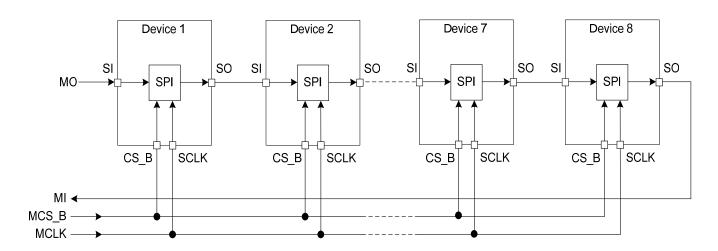


In order to select whether TER signal is output or SPI data output (OLn, Dn) signal is output, "S" signal is generated within IC and output is switched.

Daisy Chain

Plurality of devices can be connected as shown in the diagram below. CS_B signal and SCLK signal connects common signal.

SI/SO line can connect SO of Device 1 to SI of Device 2 as shown in the diagram below.



Timing chart when 8 devices are connected is shown below.

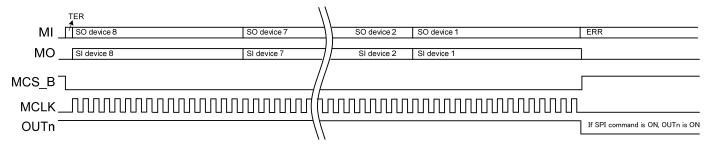


Figure 22. Timing chart when 8 devices are connected

SPI RST_B releasing sequence

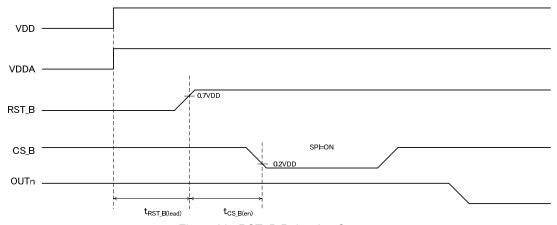


Figure 23. RST_B Releasing Sequence

Item	Signal	Minimum	Standard	Minimum	Unit
RST_B lead time ^{(1) (2)}	t _{RST_В} (lead)	1	-	-	ms
CS_B enable time ⁽¹⁾	t _{CS_B} (en)	10	-	-	μs

⁽¹⁾ Not 100% tested

⁽²⁾ RST_B L time and H time must be over $10\mu s$

SPI timing chart

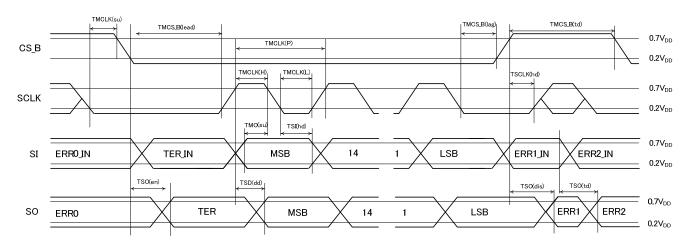


Figure 24. SPI Timing Chart

ltem	Signal	Minimum	Standard	Minimum	Unit
SCLK frequency	fSCLK	0	_	5	MHz
SCLK cycle length	TSCLK(P)	200	_	_	ns
SCLK high time	TSCLK(H)	50	_	_	ns
SCLK lo time	TSCLK(L)	50	_	-	ns
SCLK setup time	TSCLK(su)	50	_	_	ns
SCLK hold time	TSCLK(hd)	50	_	-	ns
CS_B lead time	TCS_B(lead)	250	_	-	ns
CS_B lag time	TCS_B(lag)	250	_	-	ns
Transfer delay time	TCS_B(td)	250	_	_	ns
Data setup time	TSI(su)	20	_	_	ns
Data hold time	TSI(h)	20	_	-	ns
SPI Output enable time(1)	TSO(en)	_	_	200	ns
SPI Output disable time ⁽¹⁾	TSO(dis)	_	_	250	ns
SPI Output Data delay time ⁽¹⁾	TSO(dd)	_	_	100	ns
ERR Output Through delay time ⁽¹⁾	TSO(td)	_	_	200	ns

⁽¹⁾ Not 100% tested. When SO terminal capacity=10pF.

DIR (direct) mode

Transition to direct mode is brought about by switching DIR terminal to High.

Output controlled for each input is shown below.

Further, SPI input and RST_B input are not accepted during direct mode.

Input	Controlled Output	
CS_B(IN1)	OUT1	
SI(IN2)	OUT2	
RST_B(IN3)	OUT3	
SCLK(IN4)	OUT4	
IN1(IN5)	OUT5	
IN2(IN6)	OUT6	
IN3(IN7)	OUT7	
IN4(IN8)	OUT8	

DIR (direct) mode timing chart (1)

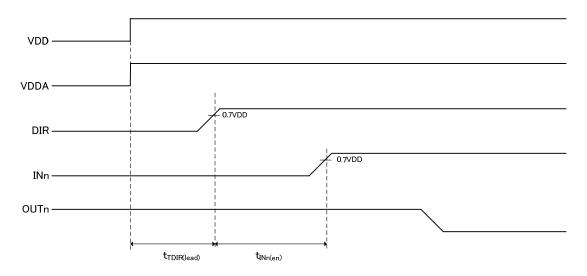


Figure 25. DIR Mode Timing Chart (1)

ltem	Signal	Minimum	Standard	Minimum	Unit
DIR lead time ⁽¹⁾	t _{DIR(lead)}	1	-	-	ms
INn enable time ⁽¹⁾	t _{INn (en)}	10	-	-	μs

(1) Not 100% tested.

DIR (direct) mode timing chart (2)

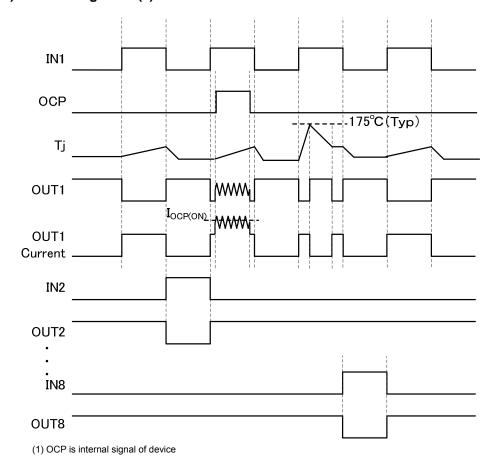


Figure 26. DIR Mode Timing Chart (2)

Direct mode operation current ($I_{DDA} + I_{DD}$) state transition

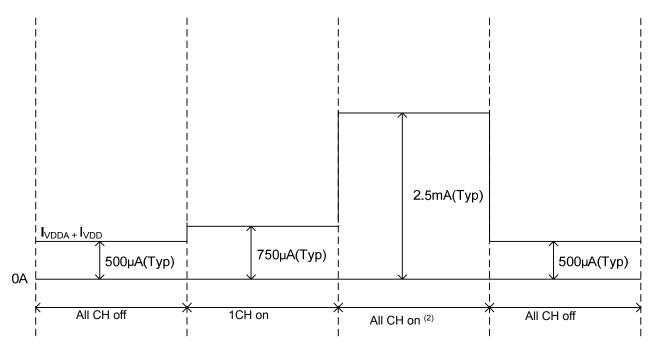


Figure 27. Operation Current State Transition Diagram

 $(2) \ Sum\ of\ P.4\ VDDA\ operation\ current\ (when\ all\ outputs\ are\ on)\ and\ VDD\ operation\ current\ (when\ all\ outputs\ are\ on).$

Power source ON/OFF sequence

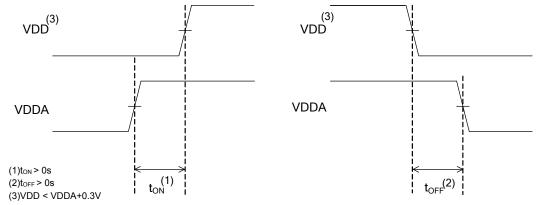
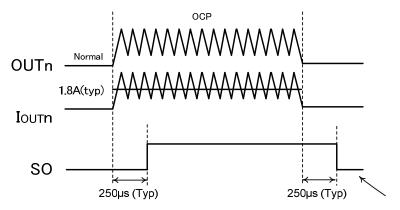


Figure 28. Power Source ON/OFF Sequence

Detection functions

① Overcurrent protection

When current of no less than 1.8 A (Typ) is flown in output transistor of from OUT1 to OUT8 in 250 μ s (Typ), error flag is output.

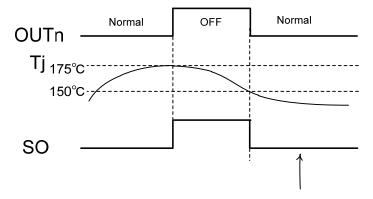


In the case of DIR and SPI mode, error flag is released 250µs after over current protection is released.

Figure 29. Overcurrent Protection Timing Chart

② Overheat protection

Junction temperature of from OUT1 to OUT8 reaches 175°C (Typ) or above, output is turned off. It is automatically turned on at 150°C (Typ) or below

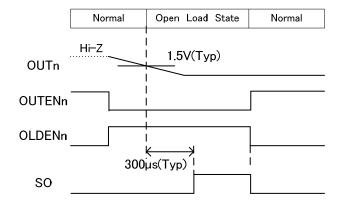


In the case of DIR and SPI mode, error flag is released after overheat protection is released.

Figure 30. Overheat Protection Timing Chart

3 Open detection

In case of enable at Open detection function⁽¹⁾, when output current of from OUT1 to OUT8 falls below 1.5 V (Typ), open detection is detected and error flag is output.

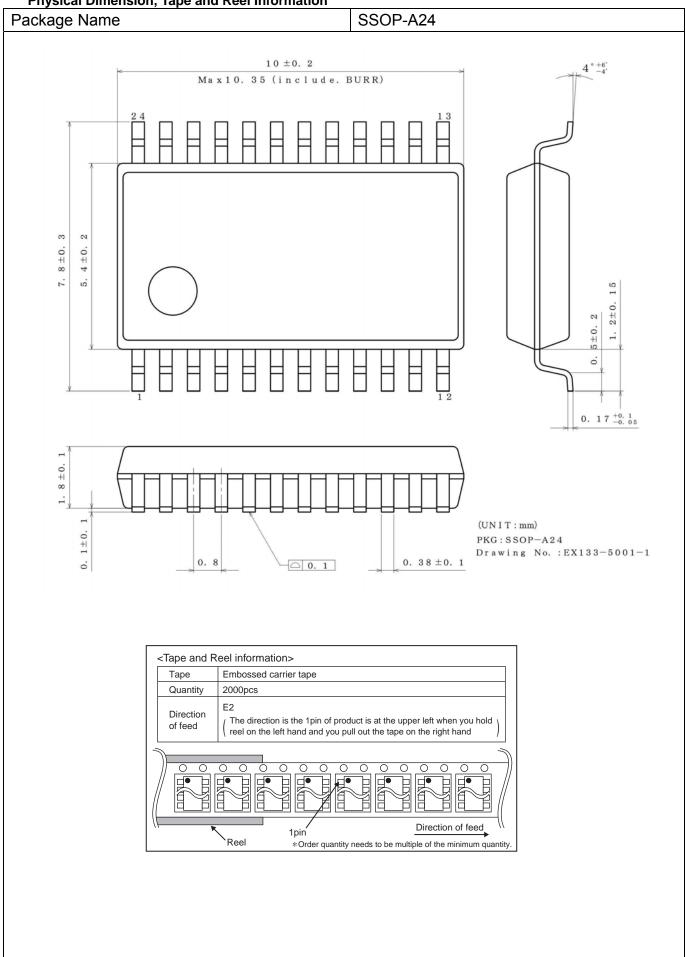


(1) As for the DIR mode, OLDENn=H(open detection function becomes effective) in OUTENn =L. As for the SPI mode, Please refer to "SI Signals" (Page 13/24).

"n" shows the channel number.

Figure 31. Open Detection Protection Timing Chart

Physical Dimension, Tape and Reel Information



Operational Notes

1) Absolute Minimum Ratings

Operating the IC over the absolute Minimum ratings may damage the IC. In addition, it is impossible to predict all destructive situations such as short-circuit modes or open circuit modes. Therefore, it is important to consider circuit protection measures, like adding a fuse, in case the IC is expected to be operated in a special mode exceeding the absolute Minimum ratings.

2) Reverse connection of power supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply terminals.

3) Power supply lines

Design the PCB layout pattern to provide low impedance ground and supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

4) Source (GND) Voltage

The voltage of the Source (GND) pin must be the lowest voltage of all pins of the IC at all operating conditions. Ensure that no pins are at a voltage below the ground pin at any time, even during transient condition.

5) Thermal consideration

Use a thermal design that allows for a sufficient margin by taking into account the permissible power dissipation (Pd) in actual operating conditions. Consider Pc that does not exceed Pd in actual operating conditions (Pc≥Pd).

Package Power dissipation : Pd (W)=(Tjmax-Ta)/ θ ja Power dissipation : Pc (W)=(Vcc-Vo) \times Io+Vcc \times Ib

Tjmax: Minimum junction temperature=150°C, Ta: Peripheral temperature[°C],

θja : Thermal resistance of package-ambience[°C /W], Pd : Package Power dissipation [W], Pc : Power dissipation [W], Vcc : Input Voltage, Vo : Output Voltage, Io : Load, Ib : Bias Current

6) Short between pins and mounting errors

Be careful when mounting the IC on printed circuit boards. The IC may be damaged if it is mounted in a wrong orientation or if pins are shorted together. Short circuit may be caused by conductive particles caught between the pins.

7) Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

8) Thermal shutdown circuit (TSD)

The IC incorporates a built-in thermal shutdown circuit, which is designed to turn off the IC when the internal temperature of the IC reaches 175°C (25°C hysteresis). It is not designed to protect the IC from damage or guarantee its operation. Do not continue to operate the IC after this function is activated. Do not use the IC in conditions where this function will always be activated.

9) Over voltage protection (active clamp)

There is a built-in over voltage protection circuit (active clamp) to absorb the induced current when inductive load is off (Power MOS = off). During active clamp and when IN=0V, TSD will not function so keep IC temperature below 150°C.

10) Over current protection circuit (OCP)

The IC incorporates an over-current protection circuit that operates in accordance with the rated output capacity. This circuit protects the IC from damage when the load becomes shorted. It is also designed to limit the output current (without latching) in the event of more than 1.5A (Typ) flow, such as from a large capacitor or other component connected to the output pin. This protection circuit is effective in preventing damage to the IC in cases of sudden and unexpected current surges. The IC should not be used in applications where the over current protection circuit will be activated continuously.

11) Testing on application boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

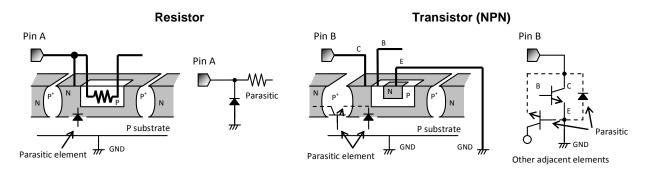
12) Regarding input pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode.

When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.



Example of monolithic IC structure

13) GND wiring pattern

When using both small-signal and large-current GND traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the GND traces of external components do not cause variations on the GND voltage. The power supply and ground lines must be as short and thick as possible to reduce line impedance.

14) Back electromotive force (BEMF)

There is a possibility that the BEMF is changed by using the operating condition, environment and the individual characteristics of motor. Please make sure there is no problem when operating the IC even though the BEMF is changed.

15) Rush Current

When power is supplied to the IC, inrush current may flow instantaneously. It is possible that the charge current from the parasitic capacitance of the internal logic may be unstable. Therefore, give a special consideration with the power coupling capacitance, power wiring, width of GND wiring, and routing of connections.

Revision History

Date Revision		Changes
06.Sep.2013	002	New Release
03.Apr.2015	003	P1 Add "AEC-Q100 qualified" to Features P3 active clamp energy condition added P4 Limit(Typ) of VDDA Operating current changed P4 Limit values of L level input current 2(CS_B) changed P5 Condition of "Open Load release voltage", "Open load detection threshold voltage" and "Open load detection time" added P6 Modify Figure 5. P7 Modify DIR(Direct)mode Diagnostic Output Truth Table P9 Characteristic Data of L level input current 2(CS_B) changed P11 Timing Chart with Inductive Load changed P12 I/O Equivalent Circuits changed P13 initial value of INn added P15 add note to SPI RST_B sequence P16 SPI timing chart and add note changed P17 DIR (direct) mode timing chart (1) and note changed P18 Figure 26. and note changed P19 timing chart of ① Overcurrent protection and ② Overheat protection changed explanation of error flag release changed P20 ③ Open detection changed P22 "7) Operation Under Strong Electromagnetic Field" added Whole page all unit changed to SI unit
		P4 Max value of PWM Output range was changed from 5kHz to 1.2kHz. P4 "DIR=5V" was removed at Condition of PWM Output range.

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(Note1) Medical Equipment Classification of the Specific Applications

1. toto 1) medical Equipment diagonication of the openitor ipplications						
JAPAN	USA	EU	CHINA			
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CLASSIV	CLASSIII	CLASSⅢ	CLASSIII			

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